

Appl. No. 10/711,140
Amdt. dated February 09, 2006
Reply to Office action of November 29, 2005

Amendments to the Drawings:

The inconsistent reference number 103 of the gate finger 102 of FIG. 4 has been corrected.

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Attachment: Replacement Sheet

1 page

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REMARKS/ARGUMENTS

Reconsideration of the present application is politely requested. Claims 1-7 and 9-12 are rejected under 35 U.S.C. 102(e) as being anticipated by Gau et al. (U.S. Pat. No.6,882,029, hereinafter Gau). Claims 8, 13-14 are rejected under 35 U.S.C. 103(a) as being unpatentable over Gau. Claims 1-3 and 5-14 remain active in the case.

In order to more particularly point out and distinct claim that which the applicant regards as his invention, independent claims 1 and 12 have been amended. No new matter in introduced by this amendment.

10 1. 102(e) rejection over Claims 1-11:

Claim 1 was rejected under 35 U.S.C. 102(e), for reasons of record that can be found on pages 3-6 in the Office action identified above, which is Part of Paper No./Mail Date 20051109. Claim 1 was rejected by the Examiner because of Gau. The applicant notices that both the Gau reference and the instant application are assigned to the same party.

15 The applicant submits that Gau teaches away that the junction varactor includes “a first ion diffusion region with first conductivity type located in said ion well at one side of said gate finger, said first ion diffusion region serving as an anode of said junction varactor”, and “a first lightly doped drain (LDD) having said first conductivity type in said ion well, and wherein said first LDD merges with said first ion diffusion region and
20 extends laterally to said gate finger”, as required by the amended claim 1. See FIG. 4 of the instant application, the LDD 113 and the ion diffusion region 112 that serves as anode of the junction varactor are of the same conductivity type. Gau merely teaches an anode P⁺ diffusion 112 encompassed by an N well 113 (see FIG. 4 of U.S. Pat. No.6,882,029). Gau doest not teach the LDD at the anode. Reconsideration of claim 1 is therefore
25 respectfully requested.

As Claims 2-3 and 5-11 are dependent upon claim 1, they should be allowable if claim 1 is allowed. Reconsideration of claims 2-3 and 5-11 is therefore politely requested.

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2. 102(e) rejection over Claims 12-14:

The applicant submits that Gau teaches away that the junction varactor includes “a P type lightly doped drain (PLDD) merging with said P⁺ ion diffusion region and extending to said first gate finger and said second gate finger”, as required by the amended claim 12. See FIG. 4 of the instant application, the LDD 113 and the ion diffusion region 112 that serves as anode of the junction varactor are of the same conductivity type. Gau merely teaches an anode P⁺ diffusion 112 encompassed by an N well 113 (see FIG. 4 of U.S. Pat. No.6,882,029). Gau does not teach the LDD at the anode. Reconsideration of claim 12 is therefore respectfully requested.

As Claims 13 and 14 are dependent upon claim 12, they should be allowable if claim 12 is allowed. Reconsideration of claims 13 and 14 is therefore politely requested.

3. 103(a) rejection over Claims 8, 13-14:

Claims 8, 13-14 were rejected under 35 U.S.C. 103(a), for reasons of record that can be found on pages 6-7 in the Office action identified above.

It is noted that the above-indicated application was filed on 8/27/2004, which is after November 29, 1999, and thus can avail to the changes made to 35 U.S.C. 103(c). As the Gau reference has a date of patent of 4/19/2005, which is after the 8/27/2004 filing date of the instant application, it is noted that the Gau reference only qualifies as a prior art reference under 35 U.S.C. 102(e)/103(a).

Both the Gau reference and the instant application are owned by the same company, “United Microelectronics Corp.” The prior art and the claimed invention were, at the time the invention was made, owned by this company, or subject to an obligation of assignment to this company. Please note the patent assignment that was electronically filed with this application, which clearly assigned this invention to United Microelectronics Corp. at the date of filing.

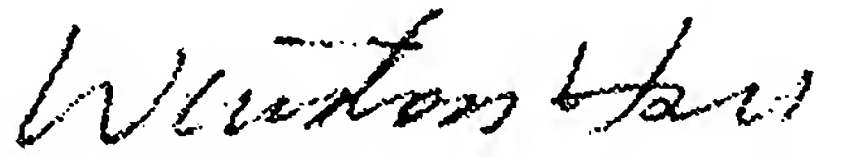
As a result of the above, the Gau reference falls under 35 U.S.C. 103(c), and so

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cannot be used to preclude patentability of the instant application. The 35 U.S.C. 103(a) rejection of claims 8, 13-14 thus cannot stand, and a quick acceptance of claims 8, 13-14 is therefore politely requested.

Applicant respectfully requests that a timely Notice of Allowance be issued in this
5 case.

Sincerely yours,



Date: 02.09.2006

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